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### FDP7030BL/FDB7030BL

## N-Channel Logic Level PowerTrench<sup>o</sup> MOSFET

### **General Description**

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

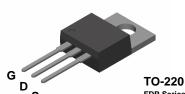
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{\text{DS(ON)}}\text{specifications}.$ 

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

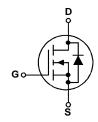
It has been optimized for low gate charge, low  $R_{\text{DS}(\text{ON})}$  and fast switching speed.

### **Features**

- 60 A, 30 V  $R_{DS(ON)} = 9 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$   $R_{DS(ON)} = 12 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- Critical DC electrical parameters specified at elevated temperature
- High performance trench technology for extremely low  $R_{\text{DS}(\text{ON})}$
- 175°C maximum junction temperature rating







TO-220 S TO-263AB FDP Series FDB Series

**Absolute Maximum Ratings** T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage		± 20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1)	60	A
	<ul><li>Pulsed</li></ul>	(Note 1)	180	
P <sub>D</sub>	Total Power Dissipation @ T <sub>C</sub> = 25°C		60	W
	Derate above 25°C		0.4	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-65 to +175	°C

### **Thermal Characteristics**

$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
FDB7030BL	FDB7030BL	13"	24mm	800 units
FDP7030BL	FDP7030BL	Tube	n/a	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	ource Avalanche Ratings (Note	1)		•		•
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15 \text{ V}, \qquad I_{D} = 60 \text{ A}$			73	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche Current				60	Α
Off Char	acteristics		<u> </u>	ı	l .	I
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	30			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		22		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μΑ
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V},  V_{DS} = 0 \text{ V}$			± 100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		-5		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On– Resistance	$V_{GS} = 10 \text{ V}, \qquad I_D = 30 \text{ A}$ $V_{GS} = 4.5 \text{ V}, \qquad I_D = 25 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 125^{\circ}\text{C}$		6.8 8.5 10.1	9 12 18	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	30			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = 10V$ , $I_{D} = 30 \text{ A}$		85		S
	Characteristics	1		l.		I
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V},  V_{GS} = 0 \text{ V},$		1760		pF
Coss	Output Capacitance	f = 1.0 MHz		440		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1		185		pF
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 15 mV, f = 1.0 MHz		1.2		Ω
Switchin	g Characteristics (Note 2)		•	•		
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 15V$ , $I_{D} = 1 A$ ,		12	22	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		12	22	ns
$t_{d(off)}$	Turn-Off Delay Time	1		30	48	ns
t <sub>f</sub>	Turn-Off Fall Time			19	33	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 15 \text{ V}, \qquad I_{D} = 30 \text{ A},$		17	24	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 5 V$		5.4		nC
$Q_{gd}$	Gate-Drain Charge	1		6.4		nC
	ource Diode Characteristics	and Maximum Ratings				
I <sub>s</sub>	Maximum Continuous Drain–Source				60	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 30 A (Note 1)		0.92	1.3	V
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 30 A,			30	nS
Q <sub>rr</sub>	Diode Reverse Recovery Charge	$d_{iF}/d_t = 100 \text{ A/}\mu\text{s}$			20	nC

#### Notes

<sup>1.</sup> Pulse Test: Pulse Width < 300μs, Duty Cycle < 2.0%

### **Typical Characteristics**

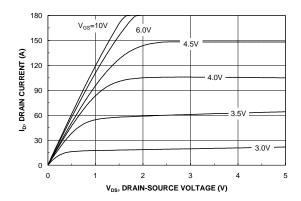


Figure 1. On-Region Characteristics.

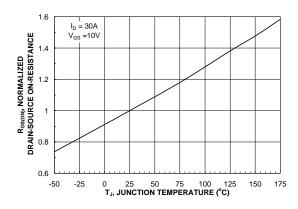


Figure 3. On-Resistance Variation with Temperature.

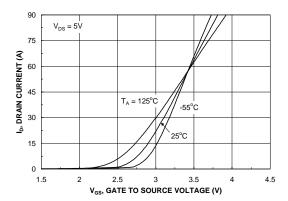


Figure 5. Transfer Characteristics.

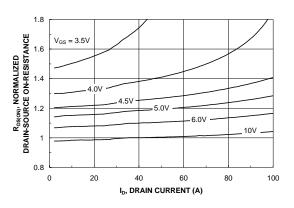


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

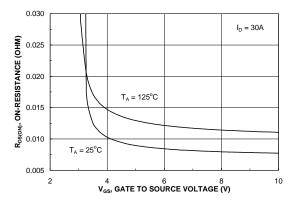


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

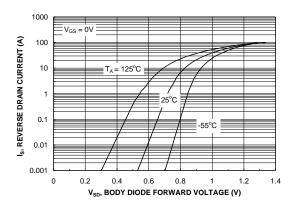
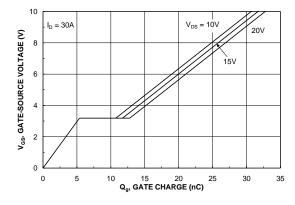


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### **Typical Characteristics**



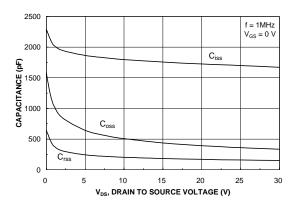
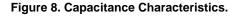
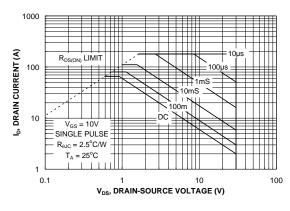


Figure 7. Gate Charge Characteristics.





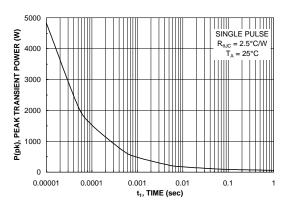


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

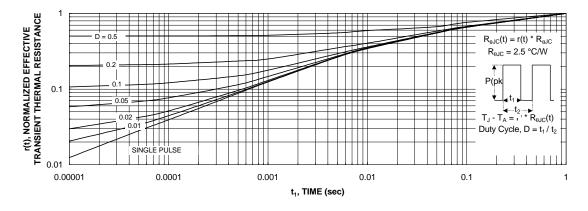


Figure 11. Transient Thermal Response Curve.

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